

EAST - [10696040.wsp:]

File View Tools Window Help

Drafts
 BRS: 31 and (BRS: 36)
 Pending
 Active
 L35: (1290) (base and drain and source and emitter)
 L36: (132) 35 and (concentration with constant)
 L37: (10) (US-6060731-S or US-6501128-S or US-55369)
 L38: (129) 36 not 37
 L39: (93) 38 and (collector and gate and (insulat\$4)
 L40: (69) 39 and (impurity adj concentration)
 L41: (68) 40 and electrode
 L42: (48) 41 and (trench or buried)

Failed
 Saved
 (1) "20040089886"
 (2) "6670658"
 (5) "6495871"
 (21) Hattori-hidetaka.in.
 (0) 6670658.URPN.
 (9266) ("IGBT" or (insulat\$3 adj gate adj bibolar adj)
 (38) ("IGBT" or (insulat\$3 adj gate adj bibolar adj
 (48) ("IGBT" or (insulat\$3 adj gate adj bibolar adj
 (38) ("IGBT" or (insulat\$3 adj gate adj bibolar adj

Browse Queue Clear
DBs USPAT, US-PGPUB, EPO, JPO, IBM, TDB
Default operator: OR Bools
 Highlight bit terms initially
41 and (trench or buried)

	U	I	P	T	P	Document ID	Issue Date	Pages	Title	Current OR	Current
1	<input checked="" type="checkbox"/>	US 20040166637	20040826	33	Manufacturing method of semiconductor device	438/270	257/E21.9;				
2	<input checked="" type="checkbox"/>	US 20040089886	20040513	NA	Power semiconductor element capable of improving short circuit withstand capability while maintaining low on-voltage and method of	257/279	257/E21.4;				
3	<input checked="" type="checkbox"/>	US 20040061518	20040401	88	Time limit function utilization	324/765	324/464				
4	<input checked="" type="checkbox"/>	US 20030205820	20031106	41	Semiconductor device and method of manufacturing the same	257/770	257/768;				
5	<input checked="" type="checkbox"/>	US 20030190788	20031009	25	Semiconductor device and its manufacturing method	438/285	257/E21.3;				
6	<input checked="" type="checkbox"/>	US 20030146473	20030807	25	Semiconductor device	257/346	257/E29.6;				
7	<input checked="" type="checkbox"/>	US 20030089966	20030515	65	Power semiconductor element capable of improving short circuit withstand capability while maintaining low on-voltage and method of	257/565	257/E21.4;				
8	<input checked="" type="checkbox"/>	US 20030306	20030306	76	Semiconductor device	257/328	257/329;				
9	<input checked="" type="checkbox"/>	US 20030042537	20030220	58	Semiconductor device having gate electrode in which depletion layer can be generated	257/344	257/330;				
10	<input checked="" type="checkbox"/>	US 20021024	20021024	58	SEMICONDUCTOR DEVICE	257/368	257/E21.4;				

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